

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

- 5     1.     (currently amended) A method for forming a light emitting diode comprising following steps:  
forming a first stack;  
forming a second reaction layer over said first stack;  
forming a second stack;  
10     forming a first reaction layer over said second stack; and  
holding together said first reaction layer and said second reaction layer by means of ~~an organic~~ a transparent adhesive layer;  
wherein the first and second reaction layers each comprise material selected from a group consisting of SiNx, ~~Ti, and Cr~~ and metal.
- 15     2.     (original) The method of claim 1 wherein the step of forming a first stack comprises following steps:  
providing a first substrate;  
forming a second contact layer on the first substrate;  
20     forming a second cladding layer on the second contact layer;  
forming an emitting layer on the second cladding layer;  
forming a first cladding layer on the emitting layer;  
forming a first contact layer on the first cladding layer; and  
forming a transparent conductive layer on the first contact layer.
- 25     3.     (original) The method of claim 2 further comprising following steps:  
removing the first substrate;  
etching the second contact layer, the second cladding layer, the emitting layer,  
first cladding layer, and the first contact layer; and  
30     forming a first electrode on the second contact layer, and a second electrode on the transparent conductive layer.

4. (original) The method of claim 2 wherein the first substrate comprises at least one material selected from a group consisting of GaP, GaAs, and Ge.
- 5 5. (original) The method of claim 2 wherein the first contact layer and the second contact layer each comprise at least one material selected from a group consisting of GaP, GaAs, GaAsP, InGaP, AlGaInP, and AlGaAs.
6. (original) The method of claim 2 wherein the first cladding layer, the emitting  
10 layer, and the second cladding layer each comprise AlGaInP.
7. (original) The method of claim 2 wherein the transparent conductive layer comprises at least one material selected from a group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, zinc tin oxide, BeAu,  
15 GeAu, and Ni/Au.
8. (cancelled)
9. (currently amended) The method of claim 1 wherein the ~~organic~~ transparent  
20 adhesive layer comprises at least one material selected from a group consisting of PI, BCB, and PFCB.
10. (original) The method of claim 1 wherein forming a second stack comprises forming a second substrate.  
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11. (original) The method of claim 10 wherein the second substrate comprises at least one material selected from a group consisting of SiC, Al<sub>2</sub>O<sub>3</sub>, glass materials, quartz, GaP, GaAsP, and AlGaAs.
- 30 12. (currently amended) The method of claim 1 wherein said first reaction layer and said second reaction layer are held together with the ~~organic~~ transparent adhesive layer by chemical bonds.

13. (original) The method of claim 12 wherein the chemical bonds are hydrogen bonds or ionic bonds.

5 14. (cancelled).

15. (new) The method of claim 1 wherein the metal comprises at least one material selected from a group consisting of Ti, and Cr.